XP152A12C0MR

Power MOSFET

■GENERAL DESCRIPTION

The XP152A12C0MR is a P-channel Power MOSFET with low on-state resistance and ultra high-speed switching characteristics.

Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.

In order to counter static, a gate protect diode is built-in.

The small SOT-23 package makes high density mounting possible.

■APPLICATIONS

● Notebook PCs

● Cellular and portable phones

● On-board power supplies

● Li-ion battery systems

■FEATURES

Low On-State Resistance : Rds(on) = 0.3Ω @ Vgs = -4.5V

: Rds(on) = 0.5Ω @ Vgs = -2.5V

Ultra High-Speed Switching

Gate Protect Diode Built-in

Driving Voltage : -2.5V

P-Channel Power MOSFET
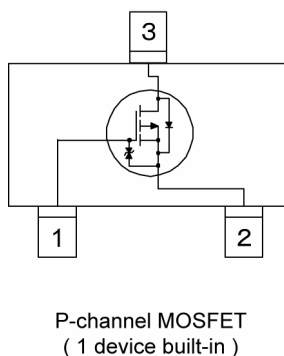
DMOS Structure

Small Package : SOT-23

■PIN CONFIGURATION

SOT-23
（TOP VIEW）
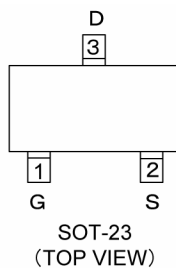
■PIN ASSIGNMENT

PIN NUMBER	PIN NAME	FUNCTION
1	G	Gate
2	S	Source
3	D	Drain

■EQUIVALENT CIRCUIT

P-channel MOSFET
(1 device built-in)

■ABSOLUTE MAXIMUM RATINGS

Ta = 25℃

PARAMETER	SYMBOL	RATINGS	UNITS
Drain - Source Voltage	Vdss	-20	V
Gate - Source Voltage	Vgss	±12	V
Drain Current　(DC)	Id	-0.7	A
Drain Current　(Pulse)	Idp	-2.8	A
Reverse Drain Current	Idr	-0.7	A
Channel Power Dissipation *	Pd	0.5	W
Channel Temperature	Tch	150	℃
Storage Temperature Range	Tstg	-55~150	℃

* When implemented on a ceramic PCB

■ELECTRICAL CHARACTERISTICS

DC Characteristics

Ta = 25℃

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain Cut-Off Current	Idss	Vds= -20V, Vgs= 0V	-	-	-10	μA
Gate-Source Leak Current	Igss	Vgs= ±12V, Vds= 0V	-	-	±10	μA
Gate-Source Cut-Off Voltage	Vgs(off)	Id= -1mA, Vds= -10V	-0.5	-	-1.2	V
Drain-Source On-State Resistance *1	Rds(on)	Id= -0.4A, Vgs= -4.5V	-	0.23	0.30	Ω
		Id= -0.4A, Vgs= -2.5V	-	0.37	0.50	Ω
Forward Transfer Admittance *1	| Yfs |	Id= -0.4A, Vds= -10V	-	1.5	-	S
Body Drain Diode Forward Voltage	Vf	If= -0.7A, Vgs= 0V	-	-0.8	-1.1	V

*1 Effective during pulse test.

Dynamic Characteristics

Ta = 25℃

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Capacitance	Ciss	Vds= -10V, Vgs=0V f= 1MHz	-	180	-	pF
Output Capacitance	Coss		-	120	-	pF
Feedback Capacitance	Crss		-	60	-	pF

Switching Characteristics

Ta = 25℃

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-On Delay Time	td (on)	Vgs= -5V, Id= -0.4A Vdd= -10V	-	5	-	ns
Rise Time	tr		-	20	-	ns
Turn-Off Delay Time	td (off)		-	55	-	ns
Fall Time	tf		-	70	-	ns

Thermal Characteristics

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal Resistance (Channel-Ambience)	Rth (ch-a)	Implement on a ceramic PCB	-	250	-	℃/W

■TYPICAL PERFOMANCE CHARACTERISTICS

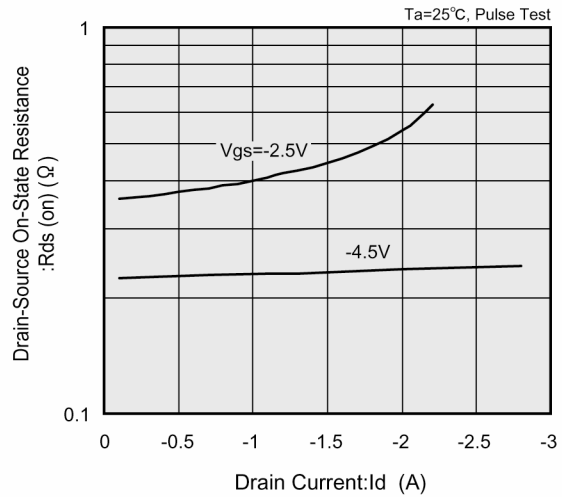### (1) Drain Current vs. Drain-Source Voltage

Ta=25℃, Pulse Test

Drain Current:Id (A)

-5V -4.5V -4V -3.5V -3V -2.5V -2V Vgs=-1.5V

Drain-Source Voltage:Vds (V)
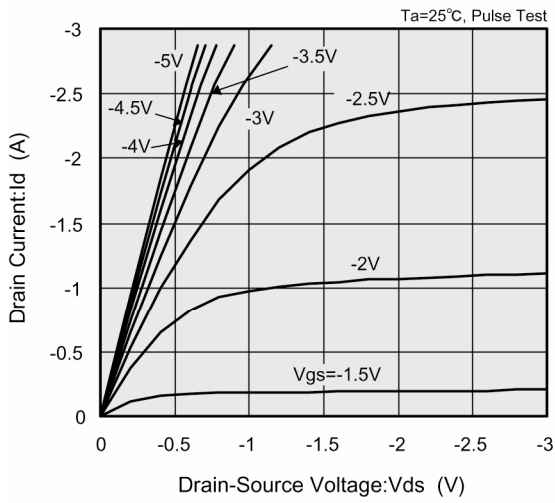
(2) Drain Current vs. Gate-Source Voltage

Vds=-10V, Pulse Test

Drain Current:Id (A)

25℃ Ta=-55℃ 125℃

Gate-Source Voltage:Vgs (V)
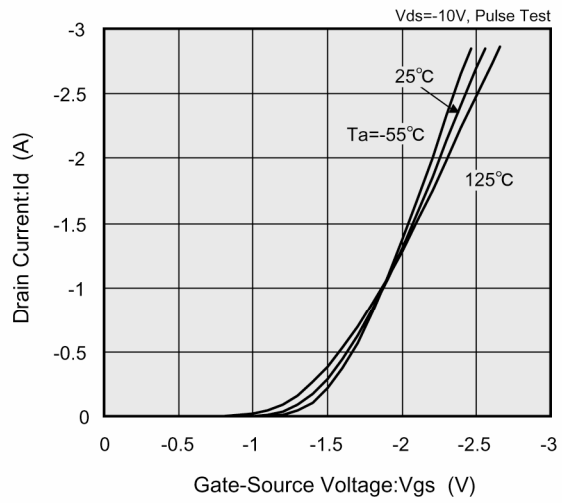
(3) Drain-Source On-State Resistance vs. Gate-Source Voltage

Ta=25℃, Pulse Test

Drain-Source On-State Resistance :Rds (on) (Ω)

Id=-0.7A -0.4A

Gate-Source Voltage:Vgs (V)
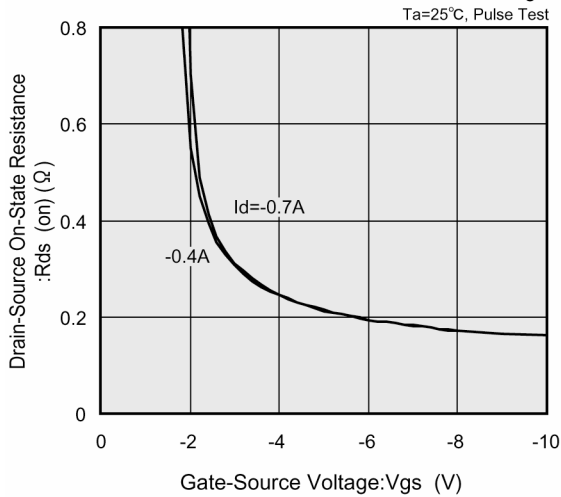
(4) Drain-Source On-State Resistance vs. Drain Current

Ta=25℃, Pulse Test

Drain-Source On-State Resistance :Rds (on) (Ω)

Vgs=-2.5V -4.5V

Drain Current:Id (A)

(5) Drain-Source On-State Resistance vs. Ambient Temperature

Pulse Test

Drain-Source On-State Resistance :Rds (on) (Ω)

Id=-0.7A Vgs=-2.5V -0.4A -0.4A, -0.7A -4.5V

Ambient Temperature:Topr (℃)
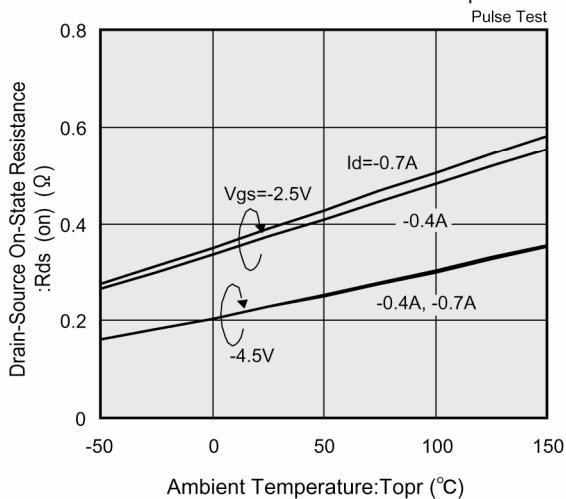
(6) Gate Source Cut-Off Voltage Variance vs. Ambient Temperature

Vds=-10V, Id=-1mA

Gate-Source Cut-Off Voltage Variance :Vgs(off) Variance (V)

Ambient Temperature:Topr (℃)

TOREX

■TYPICAL PERFOMANCE CHARACTERISTICS (Continued)

(7) Capacitance vs. Drain-Source Voltage

Vgs=0V, f=1MHz, Ta=25℃

Capacitance:C (pF) vs Drain-Source Voltage:Vds (V)

Ciss
Coss
Crss
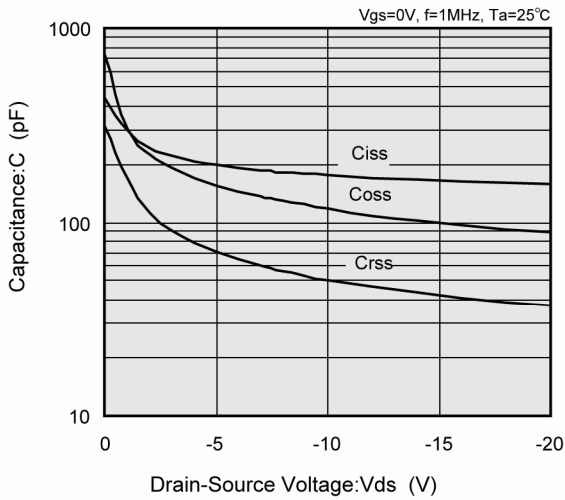
(8) SwitchingTime vs. Drain Current

Vgs=-5V, Vdd≒-10V, PW=10μs, duty≦1%, Ta=25℃

Switching Time:t (ns) vs Drain Current:Id (A)

tf
td(off)
tr
td(on)
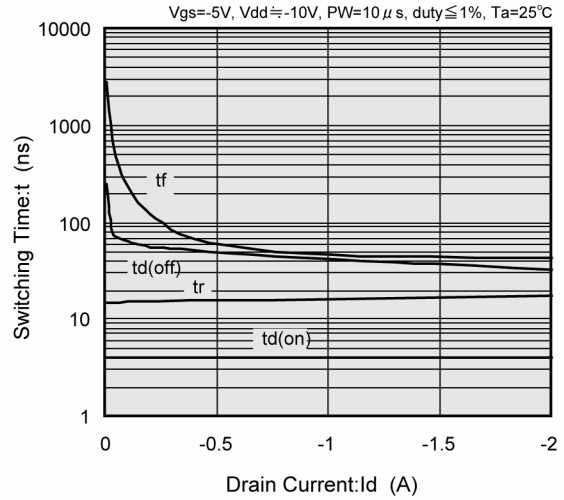
(9) Gate-Source Voltage vs. Gate Charge

Vds=-10V, Id=-0.7A, Ta=25℃

Gate-Source Voltage:Vgs (V) vs Gate Charge:Qg (nc)
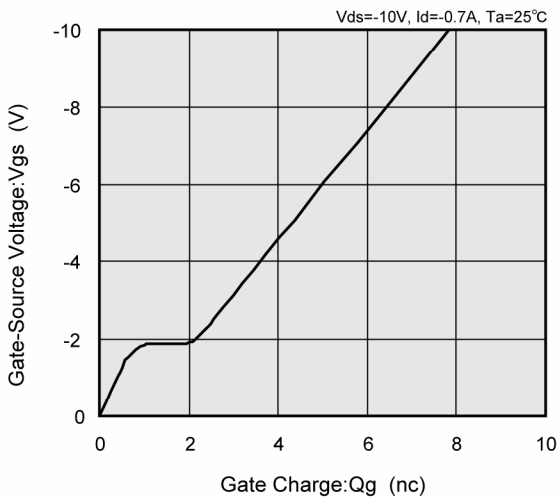
(10) Reverse Drain Current
vs. Source-Drain Voltage

Ta=25℃, Pulse Test

Reverse Drain Current:Idr (A) vs Source-Drain Voltage:Vsd (V)

-4.5V
-2.5V
Vgs=0V, 4.5V
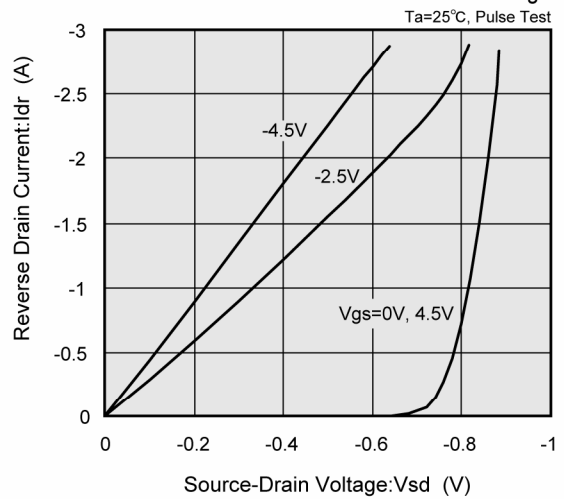
(11) Standardized Transition Thermal Resistance vs. Pulse Width

Rth(ch-a)=250℃/W (implemented on a ceramic PCB)

Standardized Transition Thermal Resistance: γs(t) vs Pulse Width:PW (s)

Single Pulse
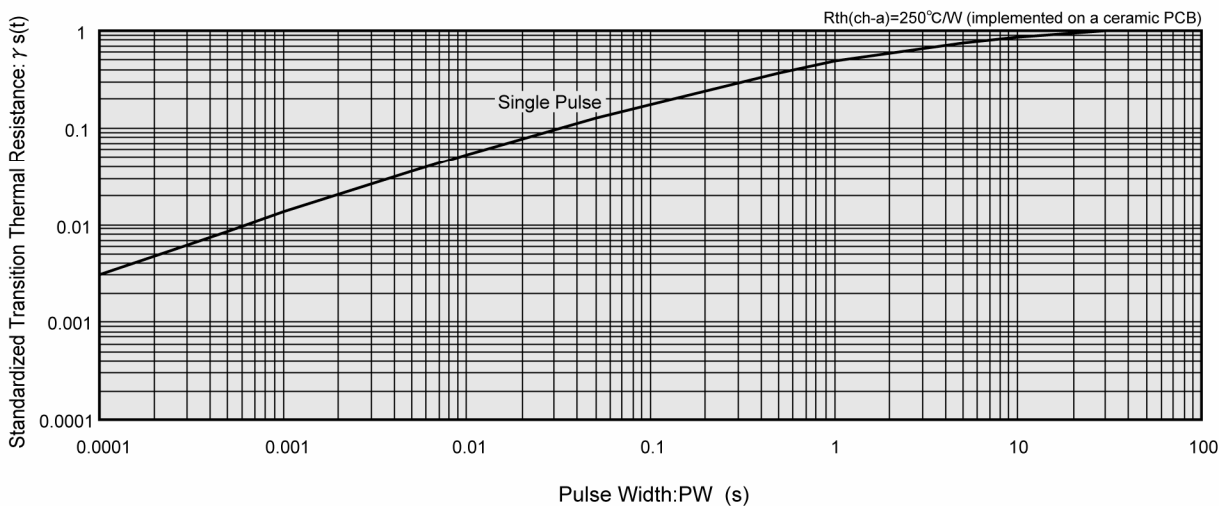
1. The products and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this catalog is up to date.

2. We assume no responsibility for any infringement of patents, patent rights, or other rights arising from the use of any information and circuitry in this catalog.

3. Please ensure suitable shipping controls (including fail-safe designs and aging protection) are in force for equipment employing products listed in this catalog.

4. The products in this catalog are not developed, designed, or approved for use with such equipment whose failure of malfunction can be reasonably expected to directly endanger the life of, or cause significant injury to, the user.
   (e.g. Atomic energy; aerospace; transport; combustion and associated safety equipment thereof.)

5. Please use the products listed in this catalog within the specified ranges.
   Should you wish to use the products under conditions exceeding the specifications, please consult us or our representatives.

6. We assume no responsibility for damage or loss due to abnormal use.

7. All rights reserved. No part of this catalog may be copied or reproduced without the prior permission of Torex Semiconductor Ltd.

TOREX SEMICONDUCTOR LTD.